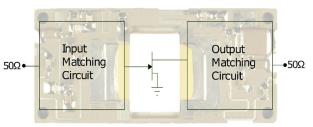


# S-Band, GaN/SiC, RF Power Amplifier Pallet

### 2.7 - 3.0 GHz | 440W typ | 63% Efficiency typ | 10.8 dB Gain typ | 50 V | 150 $\mu s$ Pulse Length, 15% Duty Cycle

IGNP2730M380 is a high power GaN-on-SiC RF power amplifier pallet that has been designed to suit the unique needs of S band radar systems. It operates over the full 2.7 - 3.0 GHz frequency range. Under 150 $\mu$ s, 15% duty cycle pulse conditions, it supplies a minimum of 330 W of peak output power, with typically >11 dB of gain and 60% efficiency. It operates from a 50 V supply voltage.



Block Diagram of IGNP2730M380

# **FEATURES**

- GaN on SiC HEMT Technology
- Output Power >330W
- Fully matched to  $50\Omega$
- High Efficiency up to 75%
- 100% RF Tested Under 150 $\mu s,$  15% duty cycle pulse conditions

# **APPLICATIONS**

S-band Radar Systems

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
RF Ouput Power	P <sub>out, rf</sub>	380 except at 3.0 GHz 330 at 3.0 GHz		520	W	P <sub>IN</sub> = 34W
Gain	G	9.9	10.8	12	dB	f = 2.7, 2.8, 2.9, 3.0 GHz
Drain Efficiency	η 45		60	75	%	150µs pulse length, 15% duty
Pulse Droop	D	-0.5		+0.15	dB	cycle
Load Mismatch Stability	VSWR-S	1.5:1				$V_{_{\rm DS}} = 50$ V, $I_{_{\rm DS}} = 100$ mA
VSWR Withstand	VSWR-LMT	3:1				

Table 1. RF Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.



## Table2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Supply Voltage	V <sub>DS</sub>	50	V	25 °C
DC Gate-Source Voltage	V <sub>gs</sub>	-8 to +0	V	25 °C
DC Drain Current	I <sub>D</sub>	20	A	25 °C
DC Gate Current	I <sub>G</sub>	81	mA	25 °C
RF Input Power	P <sub>RF,IN</sub>	34	W	25 °C
Operating Ambient Temperature	T <sub>AMB</sub>	-40 to +85	٥C	
Storage Temperature	T <sub>stg</sub>	-55 to +150	٥C	
Operating Channel Temperature	Т <sub>сн</sub>	-55 to +225	٥C	
Pallet Soldering Temperature	T <sub>SOLDER</sub>	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage

#### Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

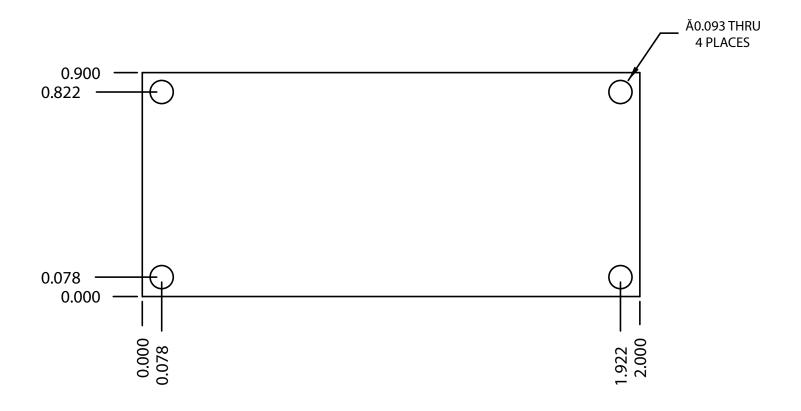
Parameter	Symbol	Min	Тур	Мах	Units	Test Conditions
Gate Pinch-Off Voltage	V <sub>P</sub>	-5.0			V	$V_{_{\rm DS}} = 50$ V, $I_{_{\rm DS}} = 1$ mA
Quiescent Gate Voltage	V <sub>Q</sub>		-2.9		V	$V_{_{\rm DS}} = 50V, I_{_{\rm DS}} = 100mA$

## Table 4. Thermal Resistance (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Тур	Max	Test Conditions
Peak Thermal Resistance, Channel to underneath side of pallet	R <sub>th</sub>	TBD	-	$P_{OUT} = 380W$ f = 2.8 GHz 150µs pulse length, 15% duty cycle $V_{DS} = 50V$ , $I_{DS} = 100mA$



DIMENSIONS





#### **ESD** Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivty Level (MSL)	0	IPC/JEDEC J-STD-020

DEFINITIONS: DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications. **MAXIMUM RATINGS** Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability. DISCLAIMER: Integra Technologies Inc. makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Integra Technologies Inc. assume any liability

arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Integra Technologies Inc. products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Integra Technologies Inc. customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Integra Technologies Inc. for any damages resulting from such improper use or sale. Copyright @ 2018.

Integra Technologies, 321 Coral Circle, El Segundo, CA 90245-4620 | Phone: 310-606-0855 | Fax: 310-606-0865 IGNP2730-REV-PR1-DS-A Page 4 Preliminary